





Support & training



SN54HC595, SN74HC595 SCLS041J – DECEMBER 1982 – REVISED OCTOBER 2021

# SNx4HC595 8-Bit Shift Registers With 3-State Output Registers

# 1 Features

- 8-bit serial-in, parallel-out shift
- Wide operating voltage range of 2 V to 6 V
- High-current 3-state outputs can drive up to 15
  LSTTL loads
- Low power consumption: 80-µA (maximum) I<sub>CC</sub>
- t<sub>pd</sub> = 13 ns (typical)
- ±6-mA output drive at 5 V
- Low input current: 1 µA (maximum)
- · Shift register has direct clear
- On products compliant to MIL-PRF-38535, all parameters are tested unless otherwise noted. On all other products, production processing does not necessarily include testing of all parameters.

# 2 Applications

- Network switches
- Power infrastructure
- LED displays
- Servers

# **3 Description**

The SNx4HC595 devices contain an 8-bit, serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for both the shift and storage register. The shift register has a direct overriding clear (SRCLR) input, serial (SER) input, and serial outputs for cascading. When the output-enable ( $\overline{OE}$ ) input is high, the outputs are in the high-impedance state.

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)
SN54HC595FK	LCCC (20)	8.89 mm × 8.89 mm
SN54HC595J	CDIP (16)	21.34 mm × 6.92 mm
SN74HC595N	PDIP (16)	19.31 mm × 6.35 mm
SN74HC595D	SOIC (16)	9.90 mm × 3.90 mm
SN74HC595DW	SOIC (16)	10.30 mm × 7.50 mm
SN74HC595DB	SSOP (16)	6.20 mm × 5.30 mm
SN74HC595PW	TSSOP (16)	5.00 mm × 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.





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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	hanges from Revision H (November 2009) to Revision I (August 2015)	Page
•	Added Applications section, Device Information table, Pin Configuration and Functions section, ESD Ra table, Thermal Information table, Feature Description section, Device Functional Modes, Application and Implementation section, Power Supply Recommendations section, Layout section, Device and Documentation Support section, and Mechanical, Packaging, and Orderable Information section	tings ว่
•	Deleted Ordering Information table.	1
•	Added Military Disclaimer to <i>Features</i> list	1
c	hanges from Revision I (August 2015) to Revision J (October 2021)	Page

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•	Updated the device information table, ESD ratings table, and the device functional modes table to fit mo	odern					
	data sheet standards	1					



# **5** Pin Configuration and Functions





Table 5-1. Pin Functions

PIN				
NAME	SOIC, PDIP, SO, CDIP, SSOP, or TSSOP	LCCC	I/O <sup>(1)</sup>	DESCRIPTION
GND	8	10	—	Ground Pin
ŌĒ	13	17	I	Output Enable
Q <sub>A</sub>	15	19	0	Q <sub>A</sub> Output
Q <sub>B</sub>	1	2	0	Q <sub>B</sub> Output
Q <sub>C</sub>	2	3	0	Q <sub>C</sub> Output
Q <sub>D</sub>	3	4	0	Q <sub>D</sub> Output
Q <sub>E</sub>	4	5	0	Q <sub>E</sub> Output
Q <sub>F</sub>	5	7	0	Q <sub>F</sub> Output
Q <sub>G</sub>	6	8	0	Q <sub>G</sub> Output
Q <sub>H</sub>	7	9	0	Q <sub>H</sub> Output
Q <sub>H'</sub>	9	12	0	Q <sub>H</sub> <sup>,</sup> Output
RCLK	12	14	I	RCLK Input
SER	14	18	I	SER Input
SRCLK	11	14	I	SRCLK Input
SRCLR	10	13	I	SRCLR Input
		1		
NC		16		No Connection
		11		
		16		
V <sub>CC</sub>	—	20	_	Power Pin

(1) Signal Types: I = Input, O = Output, I/O = Input or Output.



### 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	$I_{\rm I}$ < 0 or V <sub>I</sub> > V <sub>CC</sub>		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$V_{\rm O}$ < 0 or $V_{\rm O}$ > $V_{\rm CC}$		±20	mA
lo	Continuous output current	$V_{\rm O}$ = 0 to $V_{\rm CC}$		±35	mA
	Continuous current through V <sub>CC</sub> or GND			±70	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

### 6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	2000	V
V(ESD)		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	1000	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### **6.3 Recommended Operating Conditions**

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			SN54HC595		SN74HC595				
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		2	5	6	2	5	6	V
		V <sub>CC</sub> = 2 V	1.5			1.5			
VIH	High-level input voltage	V <sub>CC</sub> = 4.5 V	3.15			3.15			V
		V <sub>CC</sub> = 6 V	4.2			4.2			
V <sub>IL</sub> Lov	Low-level input voltage	V <sub>CC</sub> = 2 V			0.5			0.5	
		V <sub>CC</sub> = 4.5 V			1.35			1.35	V
		V <sub>CC</sub> = 6 V			1.8			1.8	
VI	Input voltage		0		V <sub>CC</sub>	0		$V_{CC}$	V
Vo	Output voltage		0		V <sub>CC</sub>	0		V <sub>CC</sub>	V
		V <sub>CC</sub> = 2 V			1000			1000	
Δt/Δv	Input transition rise or fall time <sup>(2)</sup>	V <sub>CC</sub> = 4.5 V			500			500	ns
		V <sub>CC</sub> = 6 V			400			400	
T <sub>A</sub>	Operating free-air temperature		-55		125	-40		85	°C

 All unused inputs of the device must be held at V<sub>CC</sub> or GND to ensure proper device operation. See the TI application report, Implications of Slow or Floating CMOS Inputs, SCBA004.

(2) If this device is used in the threshold region (from V<sub>IL</sub>max = 0.5 V to V<sub>IH</sub> min = 1.5 V), there is a potential to go into the wrong state from induced grounding, causing double clocking. Operating with the inputs at t<sub>t</sub> = 1000 ns and V<sub>CC</sub> = 2 V does not damage the device; however, functionally, the CLK inputs are not ensured while in the shift, count, or toggle operating modes.



### **6.4 Thermal Information**

		SN74HC595							
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	DB (SSOP)	DW (SOIC)	N (PDIP)	NS (SO)	PW (TSSOP)	UNIT	
		16 PINS	16 PINS	16 PINS	16 PINS	16 PINS	16 PINS		
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	73	82	57	67	64	108	°C/W	

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, SPRA953.

### **6.5 Electrical Characteristics**

over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS		V.	T <sub>A</sub> = 25°C			SN54HC595		SN74HC595		LINUT
PARAMETER			Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
			2 V	1.9	1.998		1.9		1.9		
		I <sub>OH</sub> = –20 μA	4.5 V	4.4	4.499		4.4		4.4		
V <sub>OH</sub>			6 V	5.9	5.999		5.9		5.9		
	$V_{I} = V_{IH} \text{ or } V_{IL}$	Q <sub>H'</sub> , I <sub>OH</sub> = -4 mA	4.5.14	3.98	4.3		3.7		3.84		V
		$Q_A - Q_H$ , $I_{OH} = -6 \text{ mA}$	4.5 V	3.98	4.3		3.7		3.84		
		Q <sub>H'</sub> , I <sub>OH</sub> = −5.2 mA	6 V	5.48	5.8		5.2		5.34		
		$Q_{A} - Q_{H}, I_{OH} = -7.8 \text{ mA}$	6 V	5.48	5.8		5.2		5.34		
	VI = VIH or VIL	I <sub>OL</sub> = 20 μA	2 V		0.002	0.1		0.1		0.1	
			4.5 V		0.001	0.1		0.1		0.1	
			6 V		0.001	0.1		0.1		0.1	
V <sub>OL</sub>		Q <sub>H'</sub> , I <sub>OL</sub> = 4 mA	4.5 V		0.17	0.26		0.4		0.33	V
		$Q_A - Q_H$ , $I_{OL}$ = 6 mA			0.17	0.26		0.4		0.33	
		Q <sub>H'</sub> , I <sub>OL</sub> = 5.2 mA	6 V		0.15	0.26		0.4		0.33	
		$Q_{A} - Q_{H}, I_{OL} = 7.8 \text{ mA}$			0.15	0.26		0.4		0.33	
lı –	$V_{I} = V_{CC} \text{ or } 0$		6 V		±0.1	±100		±1000		±1000	nA
I <sub>OZ</sub>	$V_{O} = V_{CC} \text{ or } 0, Q_{A} - Q_{H}$		6 V		±0.01	±0.5		±10		±5	μA
I <sub>CC</sub>	$V_{I} = V_{CC} \text{ or } 0, I_{O} = 0$		6 V			8		160		80	μA
Ci			2 V to 6 V		3	10		10		10	pF



### 6.6 Timing Requirements

over operating free-air temperature range (unless otherwise noted)

			V	T <sub>A</sub> = 2	T <sub>A</sub> = 25°C		SN54HC595		SN74HC595	
			VCC	MIN	MAX	MIN	MAX	MIN	MAX	UNIT
			2 V		6		4.2		5	
f <sub>clock</sub>	Clock frequency	Clock frequency			31		21		25	MHz
					36		25		29	
			2 V	80		120		100		
		SRCLK or RCLK high or low	4.5 V	16		24		20		
	Dulas duration		6 V	14		20		17		20
<sup>t</sup> w	Fuise duration		2 V	80		120		100		115
		SRCLR low	4.5 V	16		24		20		
			6 V	14		20		17		
			2 V	100		150		125		
		SER before SRCLK↑	4.5 V	20		30		25		-
			6 V	17		25		21		
		SRCLK↑ before RCLK↑ <sup>(1)</sup>	2 V	75		113		94		
			4.5 V	15		23		19		
	Set-up time		6 V	13		19		16		ns
Lsu		SRCLR low before RCLK↑	2 V	50		75		65		
			4.5 V	10		15		13		
			6 V	9		13		11		
			2 V	50		75		60		
		SRCLR high (inactive) before SRCLK↑	4.5 V	10		15		12		
			6 V	9		13		11		
		2 V	0		0		0			
t <sub>h</sub>	Hold time, SER	4.5 V	0		0		0		ns	
				0		0		0		

(1) This set-up time allows the storage register to receive stable data from the shift register. The clocks can be tied together, in which case the shift register is one clock pulse ahead of the storage register.



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SRCLK	
SER	
RCLK	
SRCLR	
ŌE	
$Q_A$	
QB	
QC	
QD	
Q <sub>E</sub>	
QF	
Q <sub>G</sub>	
Q <sub>H</sub>	
Q <sub>H</sub> ,	

NOTE: XXXXXXX implies that the output is in 3-State mode.

Figure 6-1. Timing Diagram



# 6.7 Switching Characteristics

DADAMETED	FROM	то	LOAD	v	TA	T <sub>A</sub> = 25°C		SN54HC595		SN74HC595			
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT	
				2 V	6	26		4.2		5			
f <sub>max</sub>			50 pF	4.5 V	31	38		21		25		MHz	
				6 V	36	42		25		29			
				2 V		50	160		240		200		
	SRCLK	Q <sub>H'</sub>	50 pF	4.5 V		17	32		48		40		
				6 V		14	27		41		34	20	
Lpd				2 V		50	150		225		187	ns	
	RCLK	$Q_{A} - Q_{H}$	50 pF	4.5 V		17	30		45		37		
				6 V		14	26		38		32		
				2 V		51	175		261		219		
t <sub>PHL</sub>	SRCLR	Q <sub>H'</sub>	50 pF	4.5 V		18	35		52		44	ns	
				6 V		15	30		44		37		
	ŌE			2 V		40	150		255		187		
t <sub>en</sub>		OE Q <sub>A</sub> – Q <sub>H</sub>	50 pF	4.5 V		15	30		45		37	/ ns	
				6 V		13	26		38		32		
				2 V		42	200		300		250		
t <sub>dis</sub>	ŌE	DE Q <sub>A</sub> – Q <sub>H</sub>	50 pF	4.5 V		23	40		60		50	0 ns 3	
				6 V		20	34		51		43		
				2 V		28	60		90		75		
	Q <sub>A</sub> – Q <sub>H</sub> Q <sub>H'</sub>	$Q_A - Q_H$	50 pF	4.5 V		8	12		18		15		
				6 V		6	10		15		13		
t			2 V		28	75		110		95	ns		
		Q <sub>H</sub> ,	Q <sub>H'</sub>	50 pF	4.5 V		8	15		22		19	
				6 V		6	13		19		16		
	RCLK Q <sub>A</sub> – Q <sub>H</sub>		2 V		60	200		300		250			
t <sub>pd</sub>		RCLK Q <sub>A</sub> – Q <sub>H</sub> 150 pf 4.5 V 22 40	40		60		50	ns					
					6 V		19	34		51		43	
	OE	OE Q <sub>A</sub> – Q			2 V		70	200		298		250	
t <sub>en</sub>			$Q_A - Q_H$	150 pf	4.5 V		23	40		60		50	ns
						6 V		19	34		51		43
				2 V		45	210		315		265		
t <sub>t</sub>		$Q_A - Q_H$	150 pf	4.5 V		17	42		63		53	ns	
-		1		6 V		13	36		53		45		

Over recommended operating free-air temperature range.

# 6.8 Operating Characteristics

T<sub>A</sub> = 25°C

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance	No load	400	pF



# **6.9 Typical Characteristics**



9

7 Parameter Measurement Information



PARA	METER	RL	CL	S1	S2	
	<sup>t</sup> PZH	1 40	50 pF	Open	Closed	
۹۰	tPZL	1 6 32	150 pF	Closed	Open	
•	<sup>t</sup> PHZ	<b>1 k</b> Ω	50 pE	Open	Closed	
<sup>1</sup> dis	tPLZ		эо рг	Closed	Open	
t <sub>pd</sub> or	tt		50 pF or 150 pF	Open	Open	



VOLTAGE WAVEFORMS SETUP AND HOLD AND INPUT RISE AND FALL TIMES



VOLTAGE WAVEFORMS ENABLE AND DISABLE TIMES FOR 3-STATE OUTPUTS

NOTES: A. CL includes probe and test-fixture capacitance.

 B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 C. Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following

- characteristics: PRR  $\leq$  1 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>r</sub> = 6 ns, t<sub>f</sub> = 6 ns.
- D. For clock inputs,  $f_{max}$  is measured when the input duty cycle is 50%.
- E. The outputs are measured one at a time, with one input transition per measurement.
- F. tPLZ and tPHZ are the same as tdis.
- G. tpzL and tpzH are the same as ten.
- H. tPLH and tPHL are the same as tpd.

### Figure 7-1. Load Circuit and Voltage Waveforms



### 8 Detailed Description

### 8.1 Overview

The SNx4HC595 is part of the HC family of logic devices intended for CMOS applications. The SNx4HC595 is an 8-bit shift register that feeds an 8-bit D-type storage register.

Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered. If both clocks are connected together, the shift register always is one clock pulse ahead of the storage register.

### 8.2 Functional Block Diagram



Pin numbers shown are for the D, DB, DW, J, N, NS, PW, and W packages.



### 8.3 Feature Description

The SNx4HC595 devices are 8-bit Serial-In, Parallel-Out Shift Registers. They have a wide operating current of 2 V to 6 V, and the high-current 3-state outputs can drive up to 15 LSTTL Loads. The devices have a low power consumption of 80- $\mu$ A (Maximum) I<sub>CC</sub>. Additionally, the devices have a low input current of 1  $\mu$ A (Maximum) and a ±6-mA Output Drive at 5 V.

### 8.4 Device Functional Modes

Table 8-1 lists the functional modes of the SNx4HC595 devices.

		INPUTS	;		FUNCTION		
SER	SRCLK	SRCLR	RCLK	ŌĒ	FONCTION		
Х	X	Х	Х	Н	Outputs Q <sub>A</sub> – Q <sub>H</sub> are disabled.		
Х	X	Х	Х	L	Outputs Q <sub>A</sub> – Q <sub>H</sub> are enabled.		
Х	X	L	Х	Х	Shift register is cleared.		
L	Ť	Н	х	х	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.		
Н	Ť	н	х	х	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.		
Х	X	Х	1	Х	Shift-register data is stored in the storage register.		

#### Table 8-1. Function Table



### 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

The SNx4HC595 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs.

#### 9.2 Typical Application



Figure 9-1. Typical Application Schematic

#### 9.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.



#### 9.2.2 Detailed Design Procedure

- Recommended input conditions
  - Specified high and low levels. See ( $V_{IH}$  and  $V_{IL}$ ) in Section 6.3 table.
  - Specified high and low levels. See  $(V_{IH} \text{ and } V_{IL})$  in Section 6.3 table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5 V at any valid V\_{CC}
- Recommend output conditions
  - Load currents should not exceed 35 mA per output and 70 mA total for the part
  - Outputs should not be pulled above V<sub>CC</sub>

#### 9.2.3 Application Curves





### 10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in *Section 6.3* table.

Each  $V_{CC}$  pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1 µf is recommended; if there are multiple  $V_{CC}$  pins, then 0.01 µf or 0.022 µf is recommended for each power pin. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. A 0.1 µf and a 1 µf are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

### 11 Layout

#### **11.1 Layout Guidelines**

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused, for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Figure 11-1 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or  $V_{CC}$ , whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

#### 11.2 Layout Example



Figure 11-1. Layout Diagram



### 12 Device and Documentation Support

### **12.1 Documentation Support**

### 12.1.1 Related Documentation

For related documentation, see the following:

• Texas Instruments, Implications of Slow or Floating CMOS Inputs application brief

### **12.2 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

### 12.3 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

### 12.5 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

### 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical packaging and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser based versions of this data sheet, refer to the left hand navigation.

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